

STARPOWER

SEMICONDUCTOR

IGBT

GD2400SGY120C3SN

1200V/2400A 1 in one-package

General Description

STARPOWER IGBT Power Module provides ultrafast switching speed as well as short circuit ruggedness.

It's designed for the applications such as general inverters and UPS.

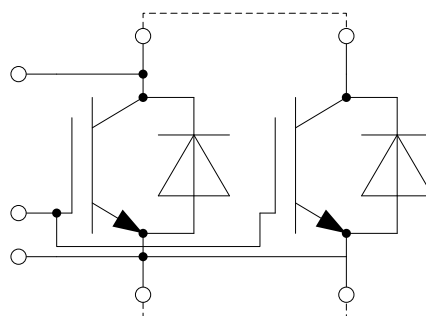
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=100^{\circ}\text{C}$	3720 2400	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	4800	A
P_D	Maximum Power Dissipation @ $T_{vj}=175^{\circ}\text{C}$	12.09	kW

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	2400	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	4800	A

Module

Symbol	Description	Value	Unit
T_{vjmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{vioP}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=2400\text{A}, V_{GE}=15\text{V}, T_{vj}=25^{\circ}\text{C}$		1.70	2.15	V
		$I_C=2400\text{A}, V_{GE}=15\text{V}, T_{vj}=125^{\circ}\text{C}$		1.95		
		$I_C=2400\text{A}, V_{GE}=15\text{V}, T_{vj}=150^{\circ}\text{C}$		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=60.0\text{mA}, V_{CE}=V_{GE}, T_{vj}=25^{\circ}\text{C}$	5.2	6.0	6.8	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_{vj}=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_{vj}=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			0.88		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		248		nF
C_{res}	Reverse Transfer Capacitance			6.96		nF
Q_G	Gate Charge	$V_{GE}=-15 \dots +15\text{V}$		18.6		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=2400\text{A}, R_{Gon}=0.5\Omega, R_{Goff}=1.5\Omega, V_{GE}=-10/+15\text{V}, T_{vj}=25^{\circ}\text{C}$		631		ns
t_r	Rise Time			238		ns
$t_{d(off)}$	Turn-Off Delay Time			1490		ns
t_f	Fall Time			156		ns
E_{on}	Turn-On Switching Loss			391		mJ
E_{off}	Turn-Off Switching Loss			434		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=2400\text{A}, R_{Gon}=0.5\Omega, R_{Goff}=1.5\Omega, V_{GE}=-10/+15\text{V}, T_{vj}=125^{\circ}\text{C}$		858		ns
t_r	Rise Time			337		ns
$t_{d(off)}$	Turn-Off Delay Time			1957		ns
t_f	Fall Time			177		ns
E_{on}	Turn-On Switching Loss			935		mJ
E_{off}	Turn-Off Switching Loss			551		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=2400\text{A}, R_{Gon}=0.5\Omega, R_{Goff}=1.5\Omega, V_{GE}=-10/+15\text{V}, T_{vj}=150^{\circ}\text{C}$		928		ns
t_r	Rise Time			352		ns
$t_{d(off)}$	Turn-Off Delay Time			2071		ns
t_f	Fall Time			194		ns
E_{on}	Turn-On Switching Loss			1066		mJ
E_{off}	Turn-Off Switching Loss			572		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_{vj}=150^{\circ}\text{C}, V_{CC}=800\text{V}, V_{CEM} \leq 1200\text{V}$		9600		A

Diode Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=2400\text{A}, V_{GE}=0\text{V}, T_{vj}=25^{\circ}\text{C}$		1.60	2.05	V
		$I_F=2400\text{A}, V_{GE}=0\text{V}, T_{vj}=125^{\circ}\text{C}$		1.70		
		$I_F=2400\text{A}, V_{GE}=0\text{V}, T_{vj}=150^{\circ}\text{C}$		1.70		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=2400\text{A},$ $-di/dt=9000\text{A}/\mu\text{s}, V_{GE}=-10\text{V},$ $T_{vj}=25^{\circ}\text{C}$		179		μC
I_{RM}	Peak Reverse Recovery Current			916		A
E_{rec}	Reverse Recovery Energy			62		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=2400\text{A},$ $-di/dt=5900\text{A}/\mu\text{s}, V_{GE}=-10\text{V},$ $T_{vj}=125^{\circ}\text{C}$		281		μC
I_{RM}	Peak Reverse Recovery Current			808		A
E_{rec}	Reverse Recovery Energy			75		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=2400\text{A},$ $-di/dt=5300\text{A}/\mu\text{s}, V_{GE}=-10\text{V},$ $T_{vj}=150^{\circ}\text{C}$		326		μC
I_{RM}	Peak Reverse Recovery Current			809		A
E_{rec}	Reverse Recovery Energy			82		mJ

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		9		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.18		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			12.4	K/kW
	Junction-to-Case (per Diode)			21.2	
R_{thCH}	Case-to-Heatsink (per IGBT)		9.6		K/kW
	Case-to-Heatsink (per Diode)		16.3		
	Case-to-Heatsink (per Module)		6.0		
M	Terminal Connection Torque, Screw M4	1.8		2.1	N.m
	Terminal Connection Torque, Screw M8	8.0		10	
	Mounting Torque, Screw M6	4.25		5.75	
G	Weight of Module		1300		g

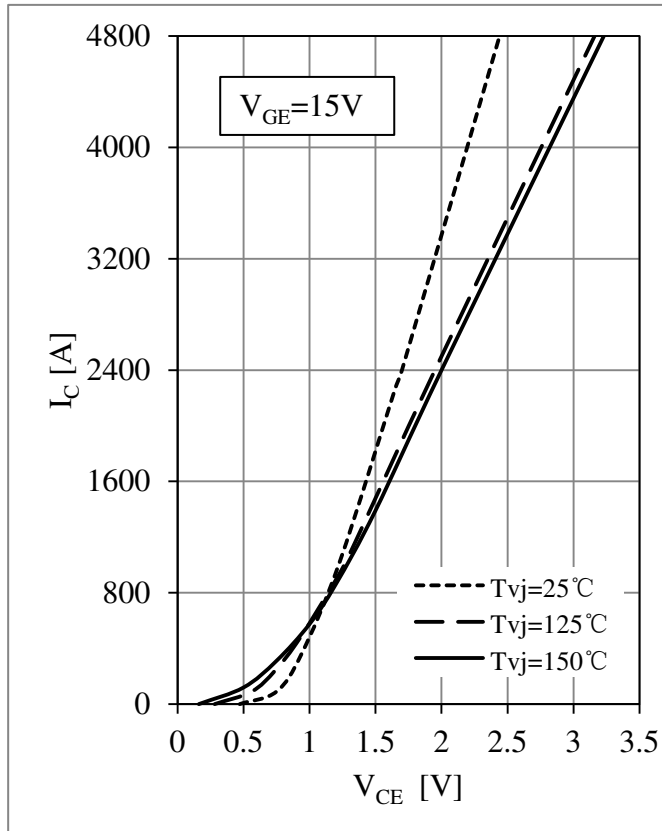


Fig 1. IGBT Output Characteristics

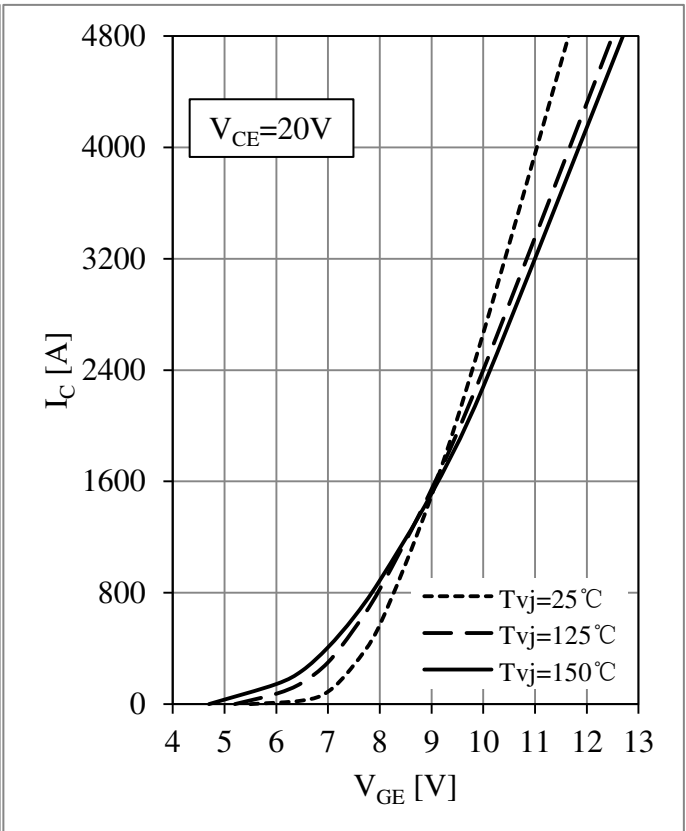
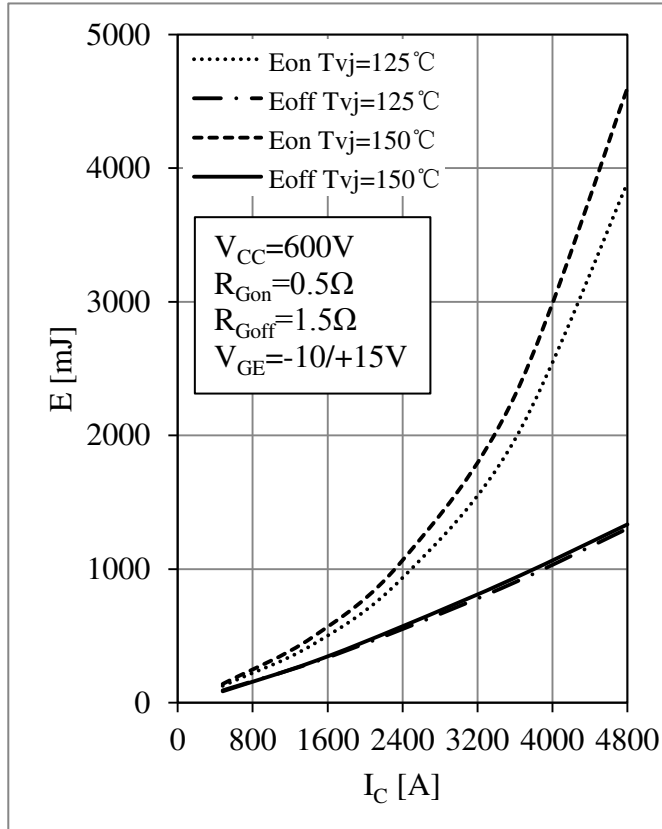
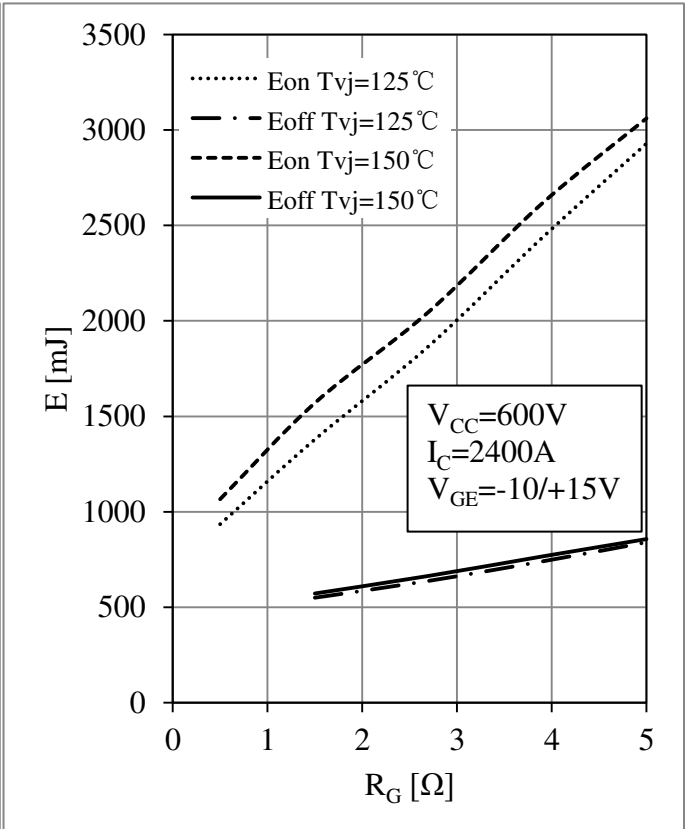


Fig 2. IGBT Transfer Characteristics

Fig 3. IGBT Switching Loss vs. I_C Fig 4. IGBT Switching Loss vs. R_G

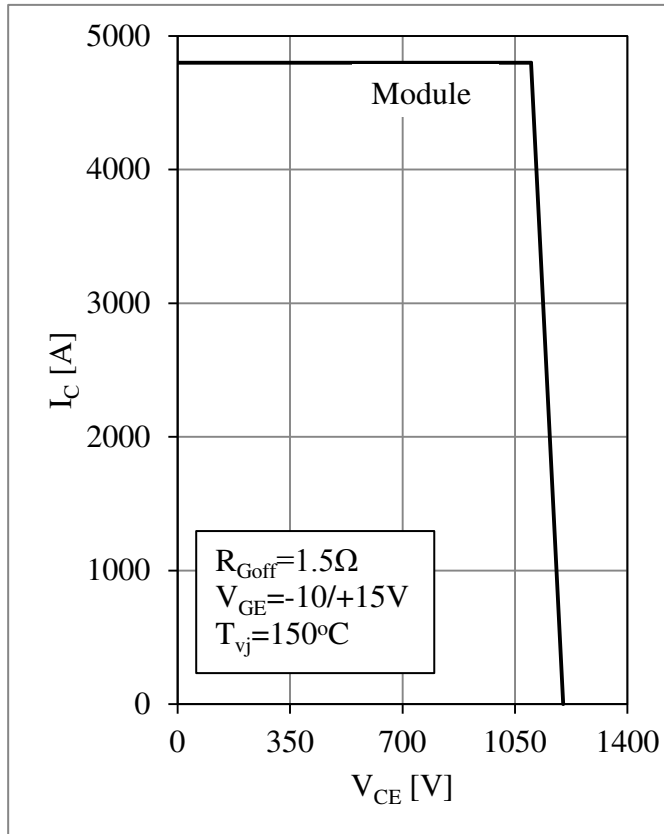


Fig 5. RBSOA

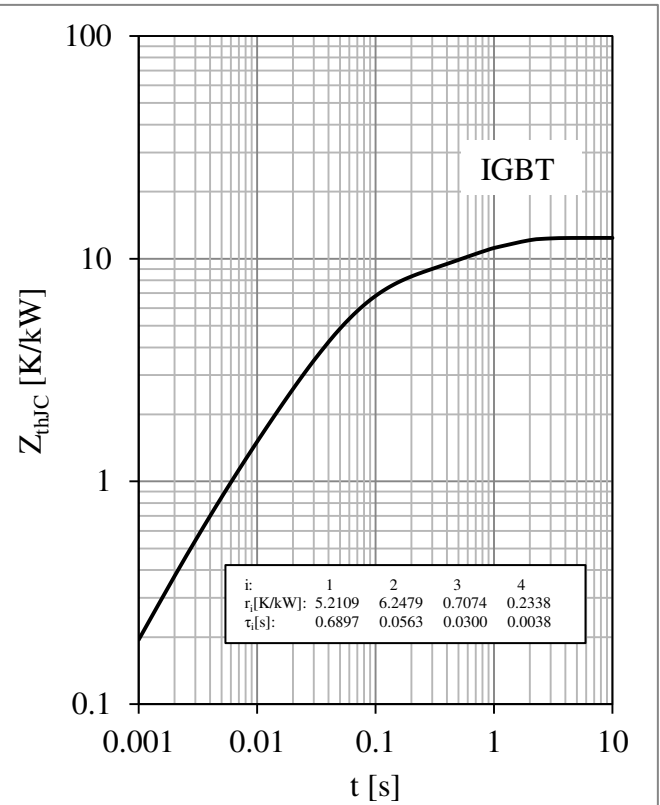


Fig 6. IGBT Transient Thermal Impedance

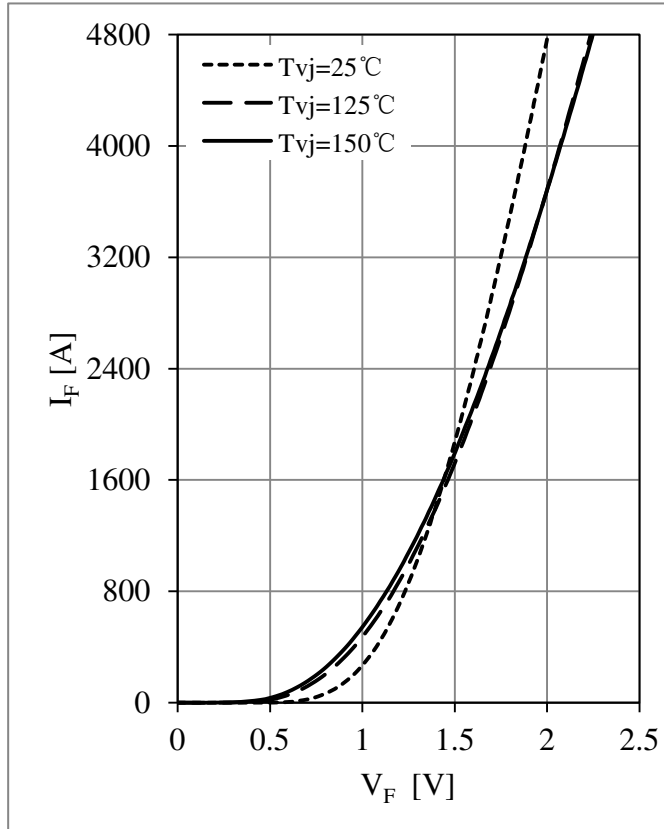
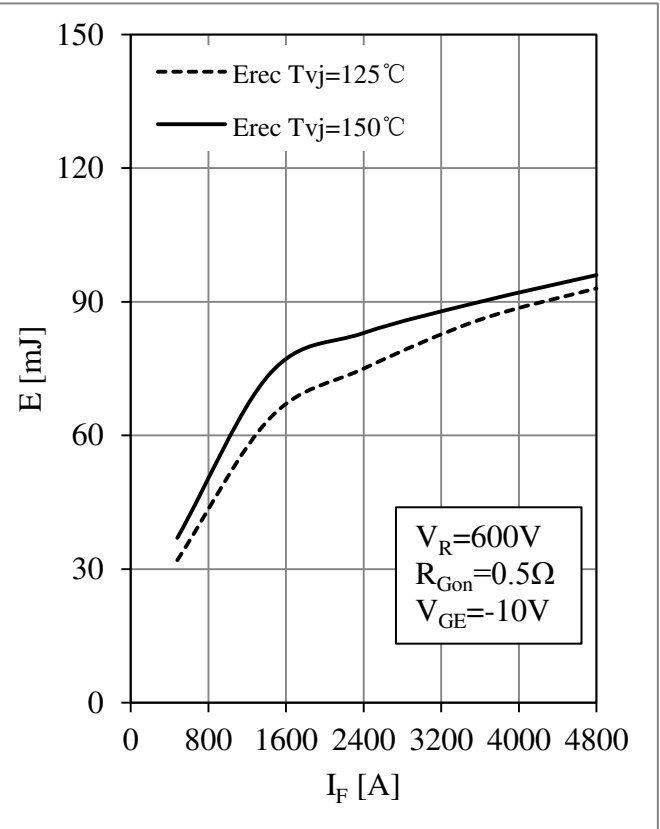


Fig 7. Diode Forward Characteristics

Fig 8. Diode Switching Loss vs. I_F

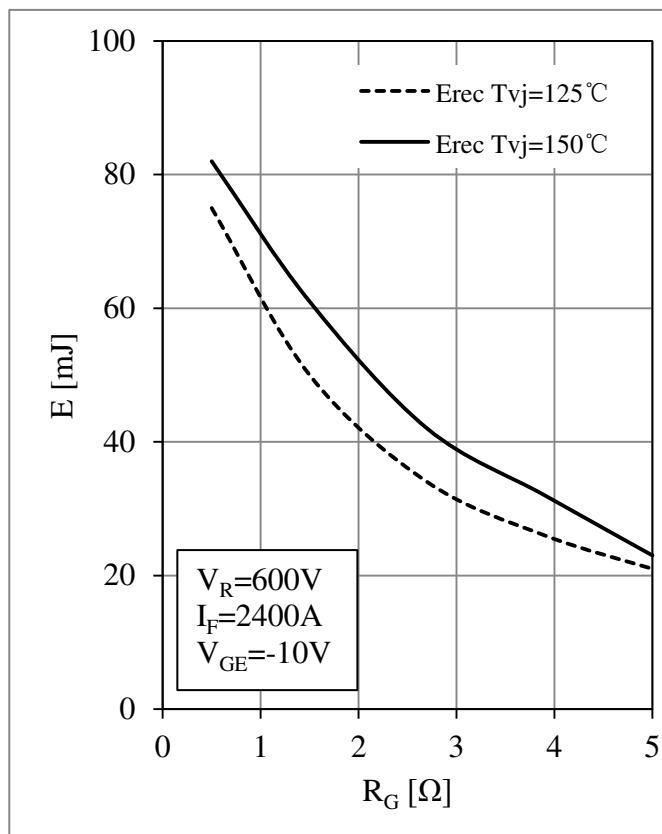
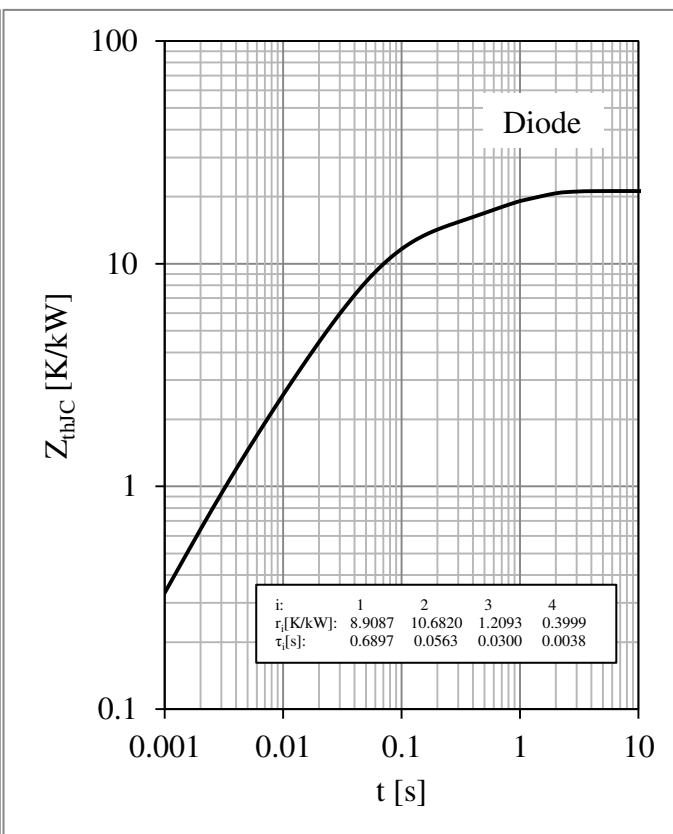
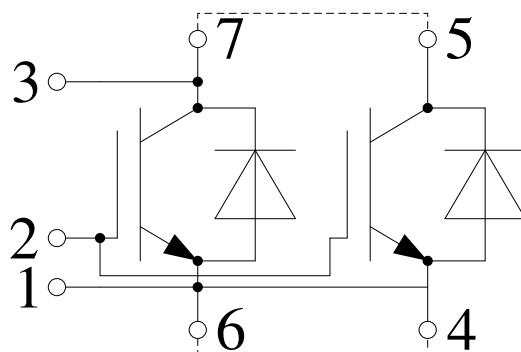
Fig 9. Diode Switching Loss vs. R_G 

Fig 10. Diode Transient Thermal Impedance

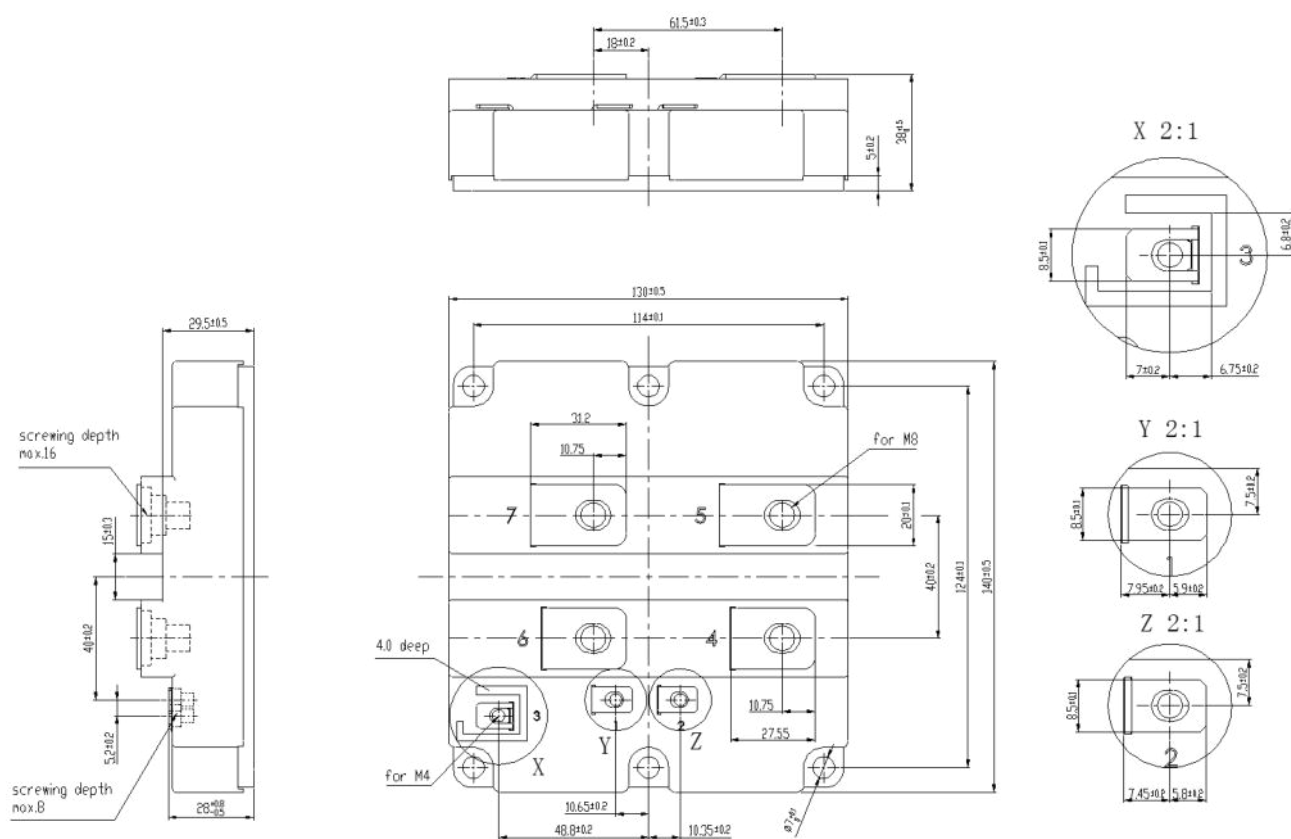
Circuit Schematic



external connection (to be done)

Package Dimensions

Dimensions in Millimeters



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